IN THE SPECIFICATION:

Please replace the paragraph beginning at page 42, line 15 with the following amended paragraph:

As shown in Fig.11, on a first electrode 12 (anode) such as ITO on a transparent substrate 1 such as glass, for example, hole transport layers 32R, 32G, 32B are formed as the charge transport layer of the element, and the hole transport layers are deposited such that each of the layers has a different thickness such as 50 nm, 70 nm, and 100 nm, for example, for each of emission parts of red, green, and blue or RGB. First, the layer is deposited in only difference thickness as a result of subtracting the common thickness from the thickness to be deposited on respective emission area of RGB. That is, the layer is deposited in a thickness of 20 nm or 50 nm, which is the thickness after subtracting a thickness of 50 nm common to respective emission areas, on G or B emission area, respectively. A material of the hole transport layer is deposited only 20 nm thick on an emission area corresponding to the green emission part G, and only 50 nm thick on the blue emission part B. Next, the same material of the hole transport layer is wholly deposited such that its thickness is 50 nm commonly for the RGB emission areas. In this way, the hole transport layer having different thickness for each of the emission areas of RGB is formed. After depositing the hole transport layer, emission layers 33R, 33G, 33B are deposited respectively, and then a common electron transport layer [[23]] 34 is deposited and thus an organic function layer is completed, and then a second electrode (cathode) 14 comprising, for example, metal is formed on the organic function layer, thereby an organic EL display panel can be produced. In this case, sheet resistance of the electron transport layer (hole transport layer) in the organic EL element is different from that of the common gap filling part, which is lower than that of the gap filling part of the element by a degree corresponding to the increased thickness.